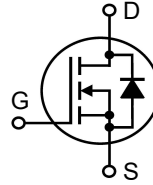


# X3-Class HiPerFET™ Power MOSFET

## IXFK400N15X3 IXFX400N15X3

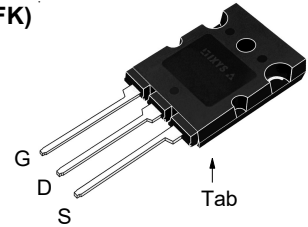
N-Channel Enhancement Mode  
Avalanche Rated



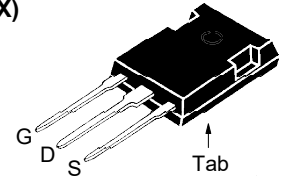
$$\begin{aligned} V_{DSS} &= 150V \\ I_{D25} &= 400A \\ R_{DS(on)} &\leq 3m\Omega \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	150	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$	150	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$ (Chip Capability)	400	A
$I_{L(RMS)}$	External Lead Current Limit	160	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$	900	A
$I_A$	$T_C = 25^\circ\text{C}$	200	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	3.5	J
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$	50	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	1250	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10s	300	$^\circ\text{C}$
$M_d$	Mounting Torque (TO-264K)	1.13/10	Nm/lb.in
$F_C$	Mounting Force (PLUS247)	20..120 / 4.5..27	N/lb
Weight	TO-264K	10	g
	PLUS247	6	g

TO-264K  
(IXFK)



PLUS247  
(IXFX)



G = Gate      D = Drain  
S = Source    Tab = Drain

### Features

- International Standard Packages
- Low  $R_{DS(ON)}$  and  $Q_G$
- Avalanche Rated
- Low Package Inductance

### Advantages

- High Power Density
- Easy to Mount
- Space Savings

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 3mA$	150		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8mA$	2.5		4.5 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			25 $\mu\text{A}$ 1.5 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			3 m $\Omega$

Symbol	Test Conditions (T <sub>J</sub> = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
<b>g<sub>fs</sub></b>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 60A, Note 1	85	145	S
<b>R<sub>Gi</sub></b>	Gate Input Resistance		2.15	Ω
<b>C<sub>iss</sub></b>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V, f = 1MHz		23.7	nF
<b>C<sub>oss</sub></b>			3730	PF
<b>C<sub>rss</sub></b>			140	pF
<b>Effective Output Capacitance</b>				
<b>C<sub>o(er)</sub></b>	Energy related	V <sub>GS</sub> = 0V V <sub>DS</sub> = 0.8 • V <sub>DSS</sub>	2200	pF
<b>C<sub>o(tr)</sub></b>	Time related		5330	pF
<b>t<sub>d(on)</sub></b>	<b>Resistive Switching Times</b> V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub> R <sub>G</sub> = 1Ω (External)		36	ns
<b>t<sub>r</sub></b>			30	ns
<b>t<sub>d(off)</sub></b>			210	ns
<b>t<sub>f</sub></b>			19	ns
<b>Q<sub>g(on)</sub></b>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub>		365	nC
<b>Q<sub>gs</sub></b>			103	nC
<b>Q<sub>gd</sub></b>			87	nC
<b>R<sub>thJC</sub></b>				0.10 °C/W
<b>R<sub>thCS</sub></b>			0.15	°C/W

#### Source-Drain Diode

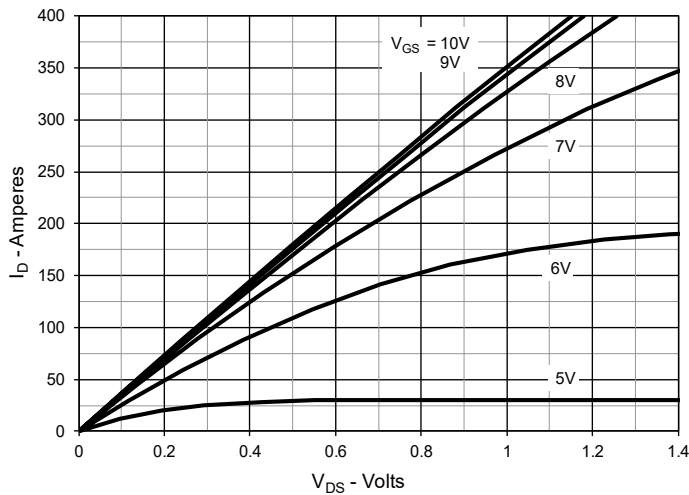
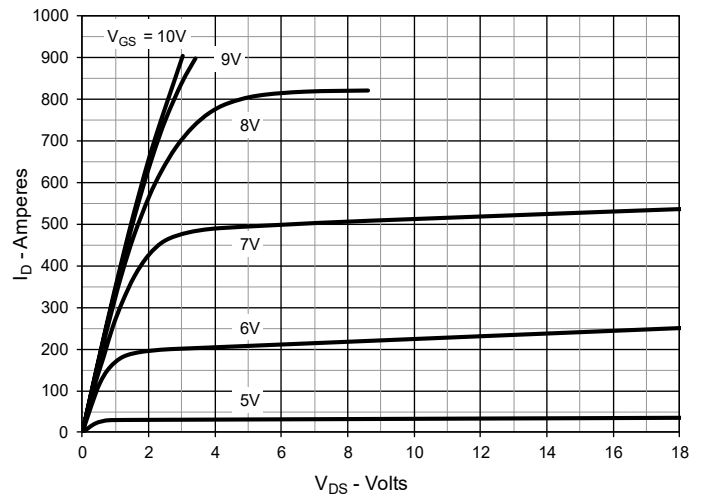
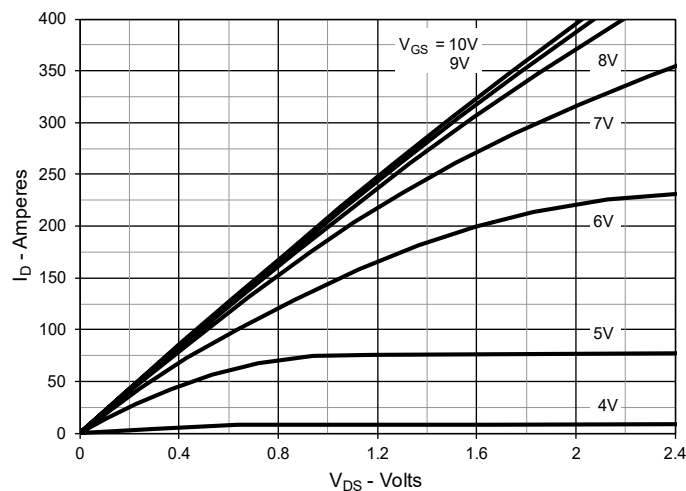
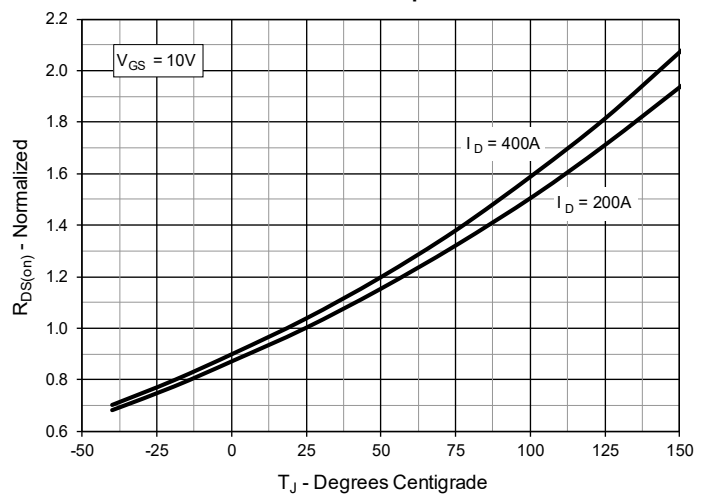
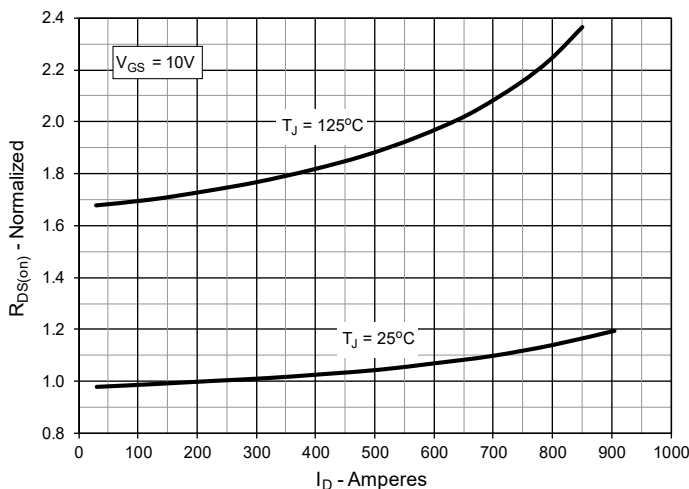
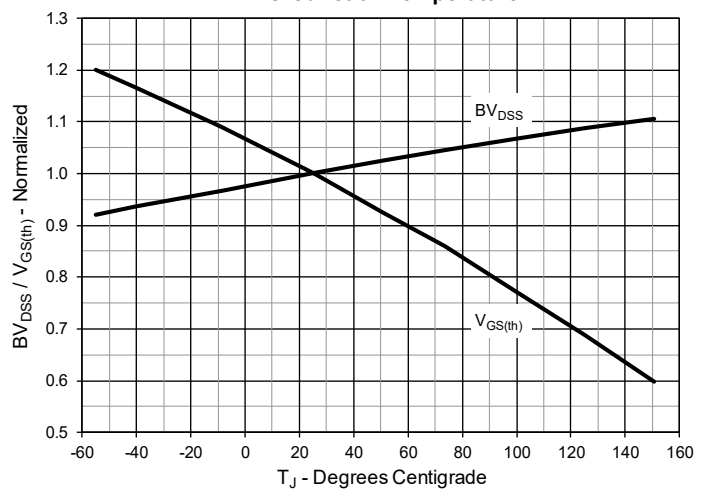
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$I_S$	$V_{GS} = 0\text{V}$			400 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			1600 A
$V_{SD}$	$I_F = 100\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1			1.4 V
$t_{rr}$	$I_F = 150\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		132	ns
$Q_{RM}$			580	nC
$I_{RM}$			8.8	A

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

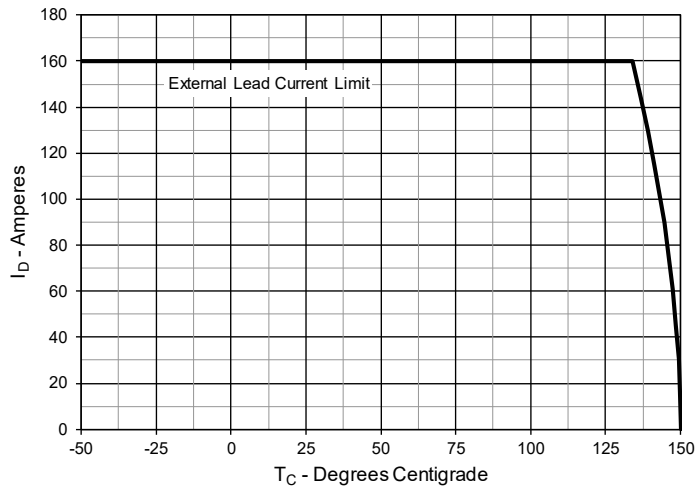
Littelfuse reserves the right to change limits, test conditions, and dimensions.

LF MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

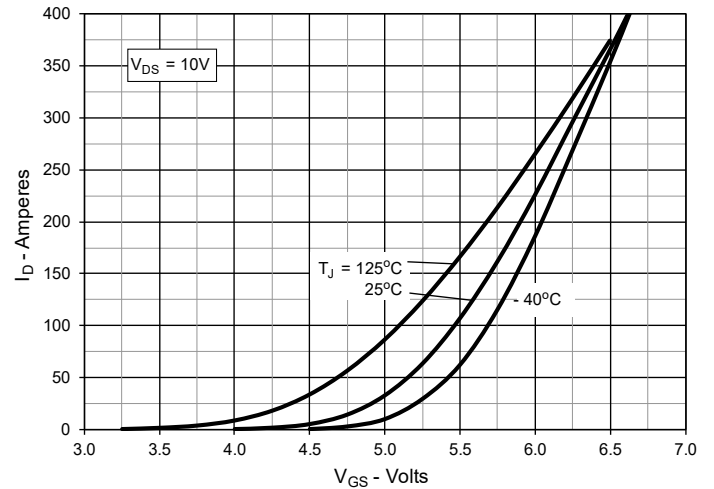
4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585	7,005,734B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728B1	6,583,505	6,710,463	6,771,478B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 200\text{A}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 200\text{A}$  Value vs. Drain Current**

**Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature**


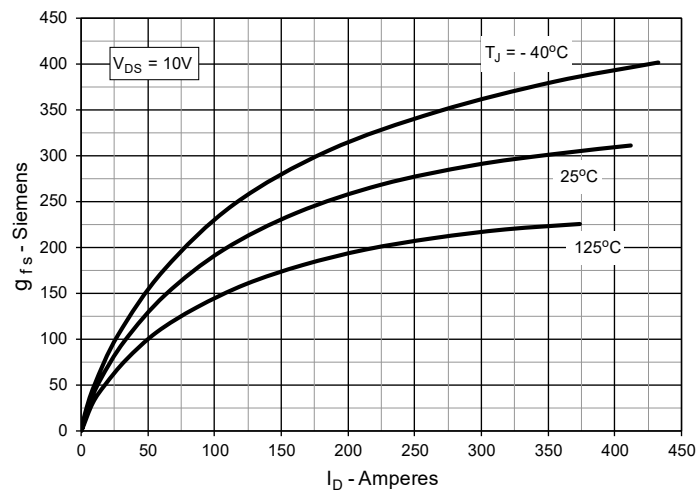
**Fig. 7. Maximum Drain Current vs. Case Temperature**



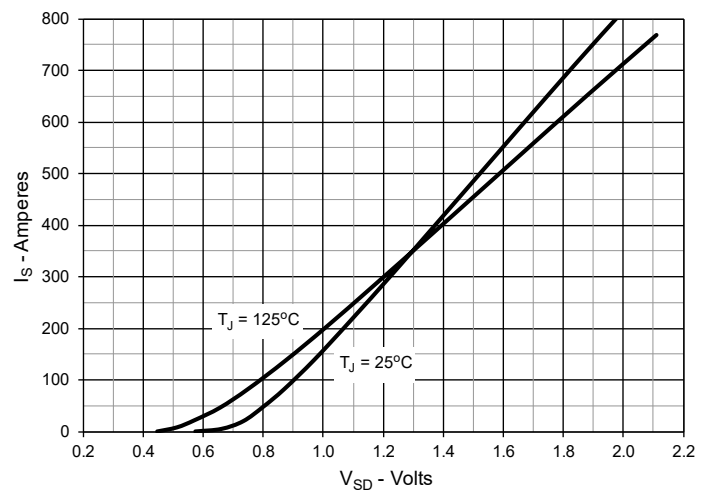
**Fig. 8. Input Admittance**



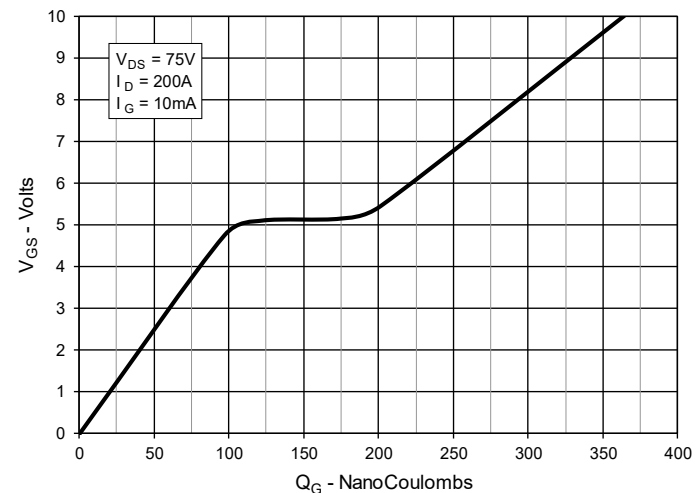
**Fig. 9. Transconductance**



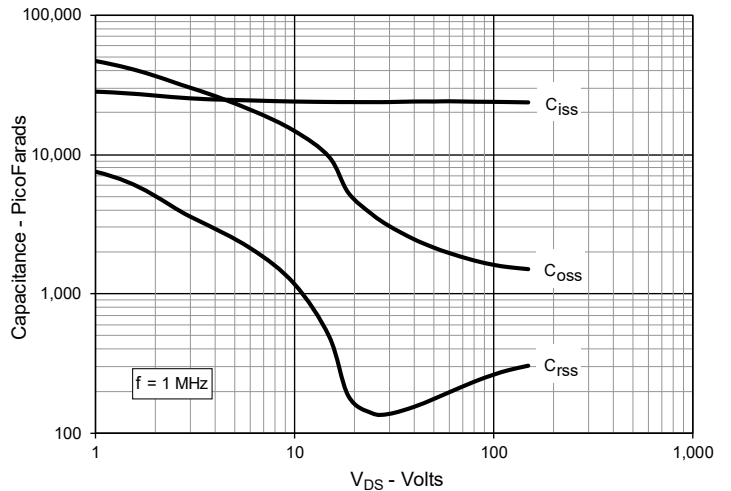
**Fig. 10. Forward Voltage Drop of Intrinsic Diode**



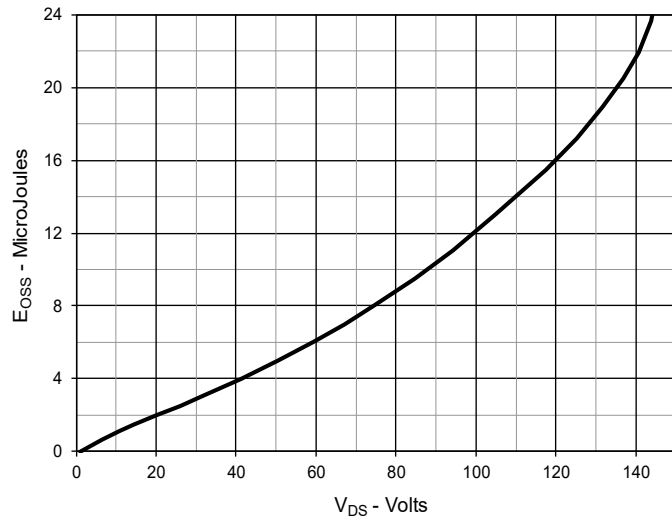
**Fig. 11. Gate Charge**



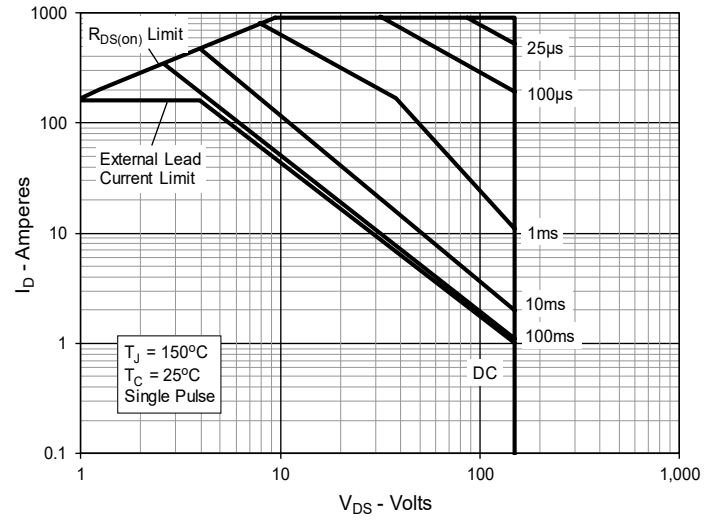
**Fig. 12. Capacitance**



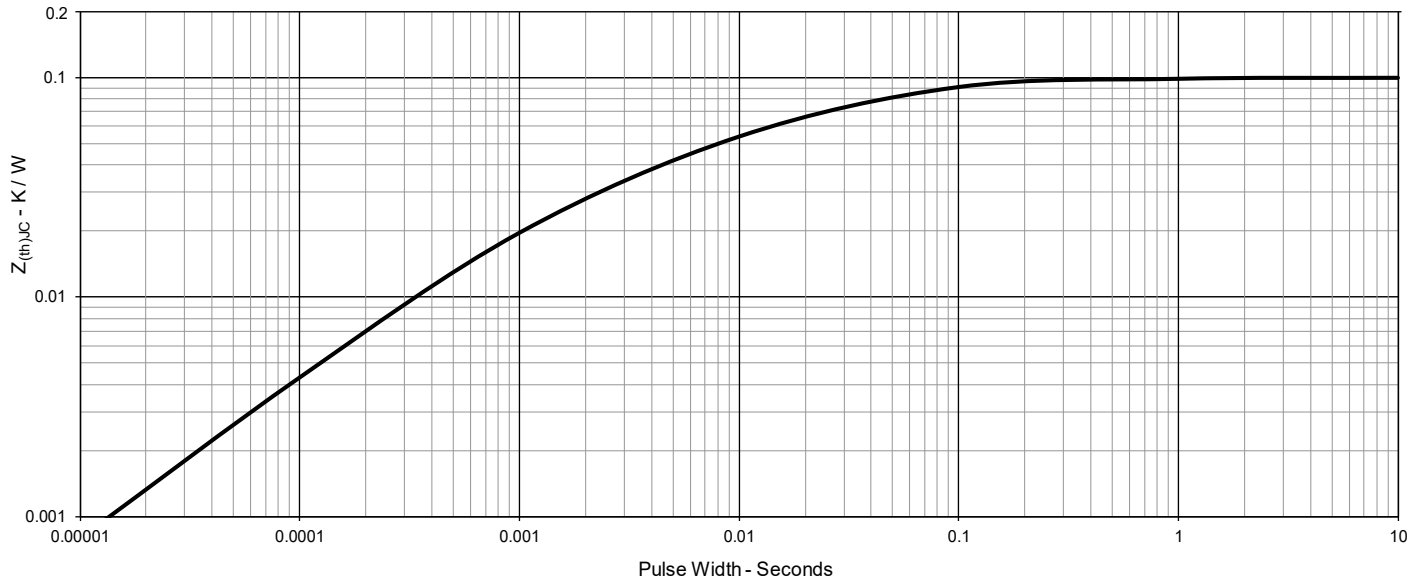
**Fig. 13. Output Capacitance Stored Energy**



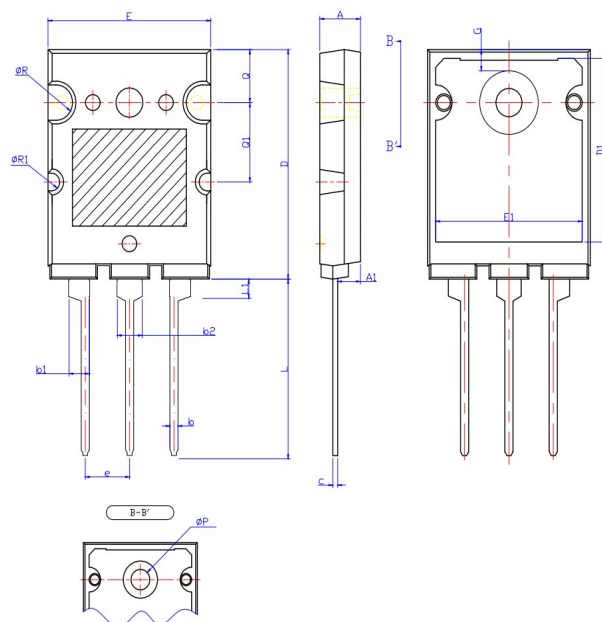
**Fig. 14. Forward-Bias Safe Operating Area**



**Fig. 15. Maximum Transient Thermal Impedance**



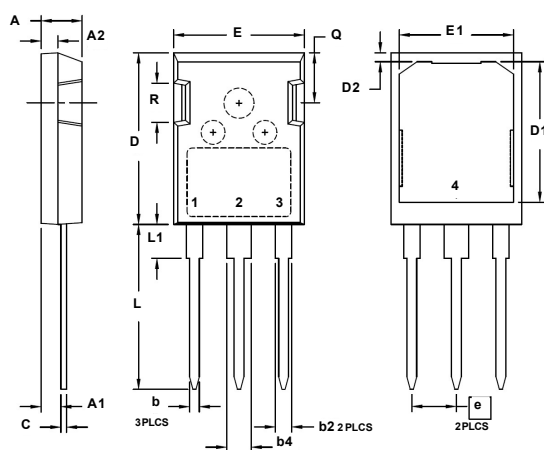
### TO-264K Outline



1 - Gate  
 2,4 - Drain  
 3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.189	0.205	4.80	5.20
A1	0.098	0.122	2.50	3.10
b	0.035	0.049	0.90	1.25
b1	0.091	0.106	2.30	2.70
b2	0.110	0.126	2.80	3.20
c	0.020	0.033	0.50	0.85
D	1.016	1.031	25.80	26.20
E	0.780	0.795	19.80	20.20
e	0.203	0.226	5.15	5.75
L	0.768	0.807	19.50	20.50
L1	0.094	0.102	2.40	2.60
ØP	0.118	0.134	3.00	3.40
Q	0.228	0.244	5.80	6.20
Q1	0.346	0.362	8.80	9.20
E1	0.701	0.717	17.80	18.20
D1	0.811	0.827	20.60	21.00
G	0.087	0.102	2.20	2.60
ØR	0.079		2.00	
ØR1	0.039		1.00	

### PLUS247™ Outline



1 - Gate  
 2,4 - Drain  
 3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.520	.560	13.08	14.22
e	.215 BSC		5.45 BSC	
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83

